

## Abstract

A method for plasma treatment etches an SiC layer with an increased etching rate and enhanced selectivities of SiC with respect to SiO<sub>2</sub> and an organic layer. An etching gas is converted into plasma to etch SiC. The etching gas may include CHF<sub>3</sub>; CHF<sub>3</sub> and N<sub>2</sub>, for example, a mixed gas of CHF<sub>3</sub>, N<sub>2</sub> and Ar; or a material having C, H and F and a material having N but without any material having O.

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